

Nanostack Impuls-Laserdioden-Array 75 W Spitzenleistung

Nanostack Pulsed Laser Diode Array 75 W Peak Power

Lead (Pb) Free Product - RoHS Compliant

SPL AH90_3



Besondere Merkmale

- 12 getrennt ansteuerbare Impuls-Laser
- Monolithischer Laserchip mit 260 µm Kanalabstand
- Austrittsöffnung pro Laserkanal 200µm × 10µm
- Nanostack Lasertechnologie beinhaltet mehrere epitaktisch integrierte Emitter
- Optische Spitzenleistung bis zu 75 W pro Kanal
- Laserwellenlänge 905 nm
- Gehäuse mit AR-vergütetem Glasfenster
- Integrierte Heizung zur Wellenlängenstabilisierung
- Betriebstemperaturbereich -40 bis +105°C

Anwendungen

- Entfernungsmessung, LIDAR
- 3D-Sensor
- Verkehrsüberwachung
- Industrie- und Automobil-Sensoren

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Norm 60825-1 behandelt werden.

Features

- 12 individually addressable pulsed lasers
- Monolithic laser die with 260 µm channel pitch
- Aperture of each laser channel 200 µm × 10 µm
- Nanostack laser technology including multiple epitaxially stacked emitters
- Optical peak power up to 75 W per laser
- Laser wavelength 905 nm
- Top looker with AR-coated glass window
- Integrated heater for wavelength stabilization
- Operating temperature range -40 to +105°C

Applications

- Range finding, LIDAR
- 3D-sensor
- Traffic surveillance
- Industrial and automotive sensors

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 "Safety of laser products"

Typ	Anzahl der Kanäle	Opt. Spitzenausgangsleistung Opt. Peak Power	Wellenlänge Wavelength	Bestellnummer Ordering Code
Type	Number of Channels			
SPL AH90_3	12	75 W	905 nm	Q65110A3900

Grenzwerte (kurzzeitiger Betrieb) ($T_A = 25^\circ\text{C}$)
Maximum Ratings (short time operation)

Parameter Parameter	Symbol Symbol	Werte Values		Einheit Unit
		min.	max.	
Spitzenausgangsleistung Peak output power	P_{peak}	—	90	W
Spitzendurchlaßstrom Peak forward current	I_F	—	40	A
Pulsbreite (Halbwertsbreite) Pulse width (FWHM)	t_p	—	100	ns
Tastverhältnis Duty cycle	<i>d.c.</i>	—	0.1	%
Sperrspannung Reverse voltage	V_R	—	3	V
Betriebsspannung der Laserheizung Operating voltage of laser heating	V_{heat}	—	5	V
Betriebstemperatur Operating temperature	T_{op}	- 40	+ 105	°C
Lagertemperatur Storage temperature	T_{stg}	- 40	+ 105	°C
Kurzzeitlagertemperatur (2 h) Short time storage temperature (2 h)	$T_{\text{stg short}}$		+ 125	°C
Löttemperatur ($t_{\text{max}} = 10$ s, 2 mm von Gehäuseunterseite) Soldering temperature ($t_{\text{max}} = 10$ s, 2 mm from bottom edge of case)	T_s	—	+ 260	°C

Optische Kennwerte ($T_A = 25^\circ\text{C}$)
Optical Characteristics

Parameter Parameter	Symbol Symbol	Werte Values			Einheit Unit
		min.	typ.	max.	
Zentrale Emissionswellenlänge ¹⁾ Emission wavelength ¹⁾	λ_{peak}	895	905	915	nm
Spektralbreite (Halbwertsbreite) ¹⁾ Spectral width (FWHM) ¹⁾	$\Delta\lambda$	—	7	9	nm
Spitzenausgangsleistung ¹⁾ Peak output power ¹⁾	P_{op}	66	75	85	W
Kennliniensteigung im Bereich 25...35 A Slope of LI-curve in the range 25...35 A	$\Delta P/\Delta I$	1.6	2.0	2.4	W/A
Betriebsspannung ¹⁾ Operating voltage ¹⁾	V_{op}	7	9	12	V
Anstiegs- und Abfallzeit (10%...90%) Rise and fall time (10% ... 90%) (electrical pulse: $I=30\text{A}$, $t_r, t_f = 0.8 \text{ ns}$)	t_r, t_f	—	—	3	ns
Anzahl Kanäle Number of channels	N	—	12	—	—
Austrittsöffnung pro Kanal Aperture size for each channel	$w \times h$	—	200×10	—	μm
Kanalabstand Gap between channels	d	—	60	—	μm
Strahldivergenz (Halbwertsbreite) parallel zum pn-Übergang Beam divergence (FWHM) parallel to pn-junction	θ_{\parallel}	8	11	14	Grad deg.
Strahldivergenz (Halbwertsbreite) senkrecht zum pn-Übergang Beam divergence (FWHM) perpendicular to pn-junction	θ_{\perp}	20	25	30	Grad deg.
Temperaturkoeffizient der Wellenlänge Temperature coefficient of wavelength	$\partial\lambda / \partial T$	—	0.28	0.31	nm/K
Temperaturkoeffizient der opt. Ausgangsleistung (25...105°C) Temperature coefficient of optical power (25...105°C)	$\Delta W/\Delta T$	—	-0.27	-0.32	W/K

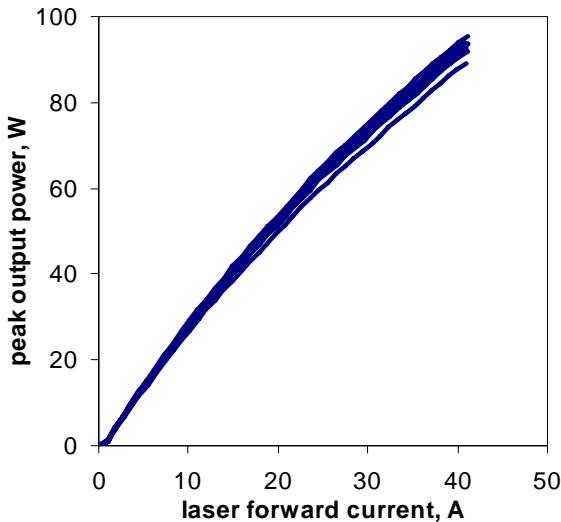
Optische Kennwerte ($T_A = 25^\circ\text{C}$)**Optical Characteristics (cont'd)**

Parameter Parameter	Symbol Symbol	Werte Values			Einheit Unit
		min.	typ.	max.	
Elektrischer Widerstand der Laserheizung Electrical resistance of laser heating	R_{heat}	16	20	24	Ohm
Zentrale Emissionswellenlänge im Betriebstemperaturbereich -40...+30°C bei Lasermodul mit Heizung Emission wavelength in operating temperature range -40...+30°C for laser module with heating	$\lambda_{\text{peak, heat}}$	895	—	—	nm

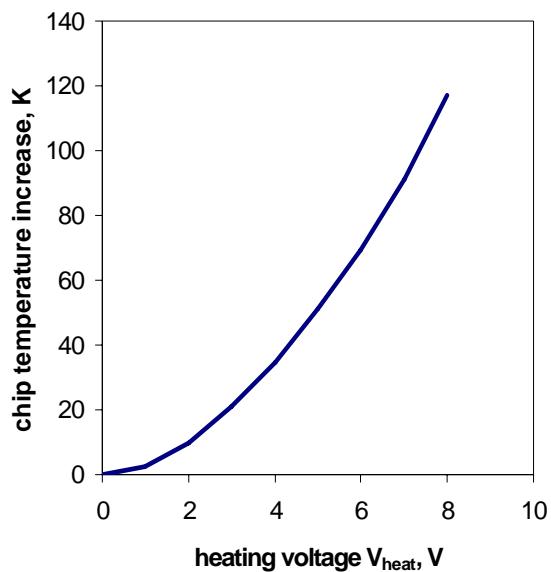
¹⁾ Standardbetriebsbedingungen beziehen sich auf eine Pulsbreite von 10-20 ns bei einer Frequenz von 1kHz und einem Betriebsstrom von 31 A bei $T_A = 25^\circ\text{C}$.

Standard operating conditions refer to pulses of 10-20 ns pulse width at 1 kHz rate with 31 A operating current at $T_A = 25^\circ\text{C}$.

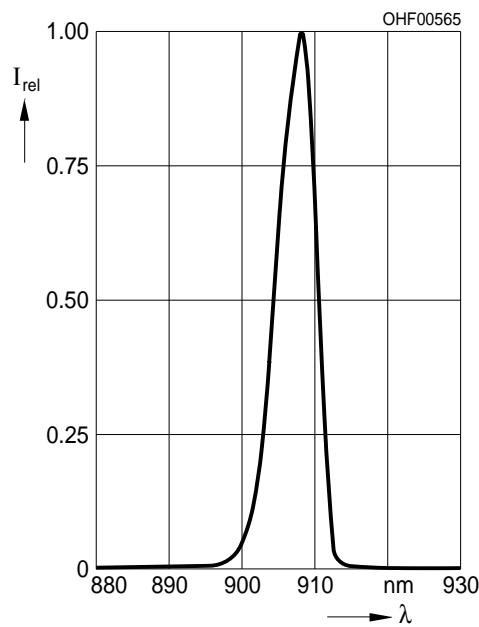
Optical output power P_{opt} vs. forward current I_F for all 12 channels ($T_A = 25^\circ\text{C}$)



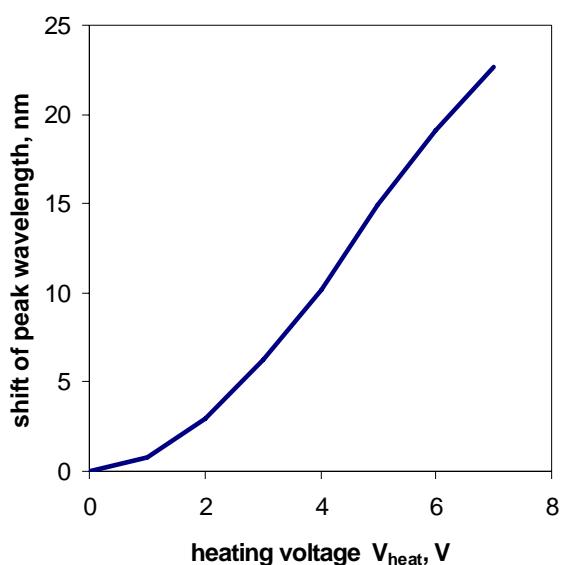
Chip temperature increase vs. heating voltage V_{heat}



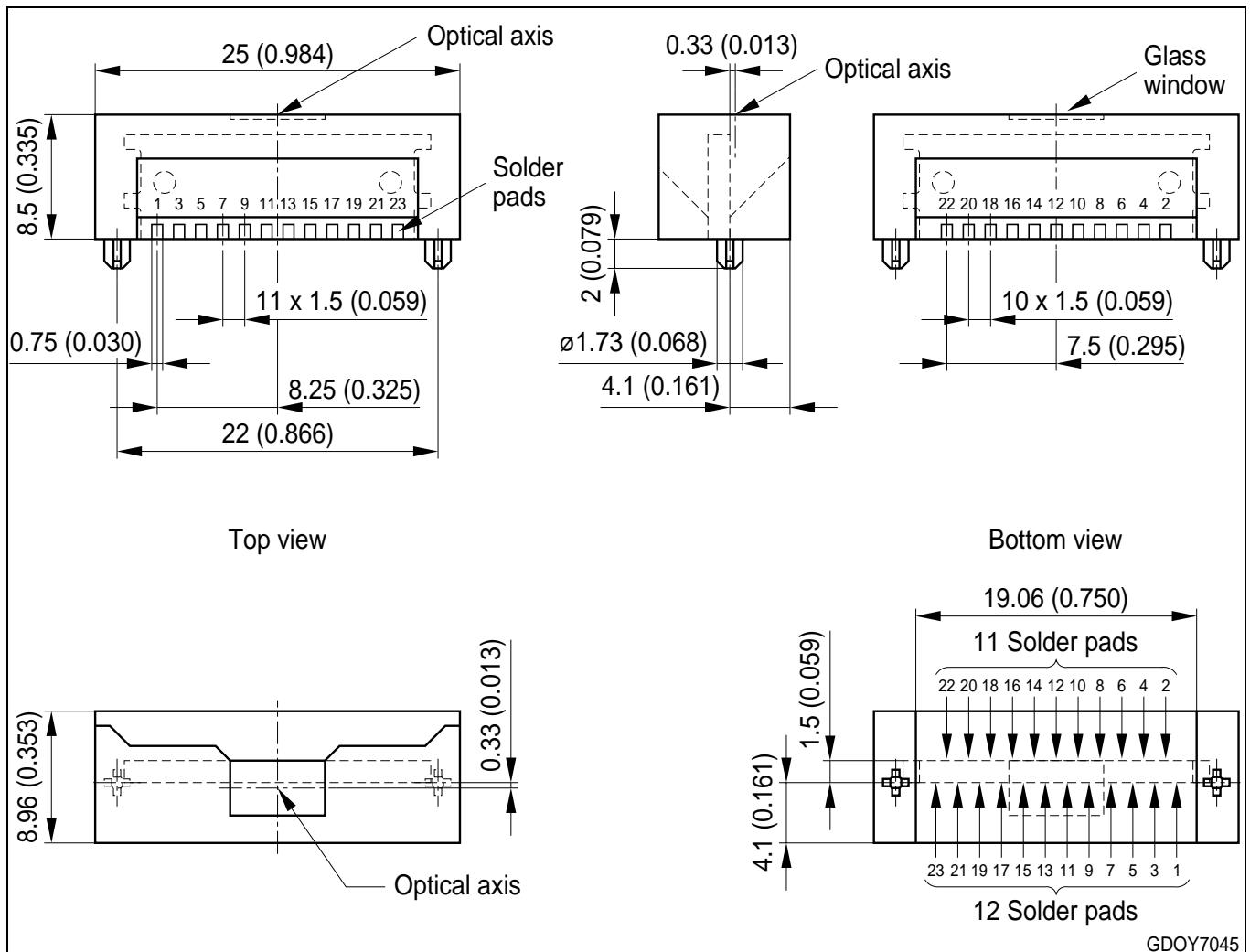
Optical spectrum, relative intensity I_{rel} vs. wavelength λ ($T_A = 25^\circ\text{C}$, $P_{\text{opt}} = 75\text{ W}$)



Shift of peak wavelength vs. heating voltage V_{heat}



Maßzeichnung
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Belegung der Lötpads / Plnning of solder pads

Lötpad / Solder pad	Funktion / Function
1	Heizung + / Heating +
2	NTC +
3	nicht verbunden / not connected
4	Anode Kanal 1 / Anode Channel 1
5	Masse / GND
6	Anode Kanal 2 / Anode Channel 2
7	nicht verbunden / not connected
8	Anode Kanal 3 / Anode Channel 3
9	Anode Kanal 4 / Anode Channel 4
10	Masse / GND
11	Anode Kanal 5 / Anode Channel 5
12	Anode Kanal 6 / Anode Channel 6
13	Anode Kanal 7 / Anode Channel 7
14	Anode Kanal 8 / Anode Channel 8
15	Masse / GND
16	Anode Kanal 9 / Anode Channel 9
17	Anode Kanal 10 / Anode Channel 10
18	nicht verbunden / not connected
19	Anode Kanal 11 / Anode Channel 11
20	Masse / GND
21	Anode Kanal 12 / Anode Channel 12
22	nicht verbunden / not connected
23	Heizung - , NTC - / Heating - , NTC -

Published by
OSRAM Opto Semiconductors GmbH
Wernerwerkstrasse 2, D-93049 Regensburg
www.osram-os.com
© All Rights Reserved.

The information describes the type of component and shall not be considered as assured characteristics.
Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components¹, may only be used in life-support devices or systems² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

EU RoHS and China RoHS compliant product



此产品符合欧盟 RoHS 指令的要求；

按照中国的相关法规和标准，不含有毒有害物质或元素。